SLR Fluorine Etcher: recipe = SiVertHF

(developed by Bill Mitchell, Nanofab process group)

Substrate structure	Si(500nm)/SiO2(2000nm)/Si(sub0
Masking resist	maN-2405(~120nm)
Plasma Powers	
ICP	950W
CCP[bias]	15W
Gas Flows	
C4F8	60sccm
SF6	24sccm
CF4	27sccm
Gas Pressures	
Etch step	20mTorr
Ignition step	10mTorr (SF6 flow set low to 10sccm)
Etch Data	
Etch Rate (laser monitor)	Si ~ 300-350nm/min, SiO2 ~ 30-35nm/min
Etch angle	~89-90 degrees







